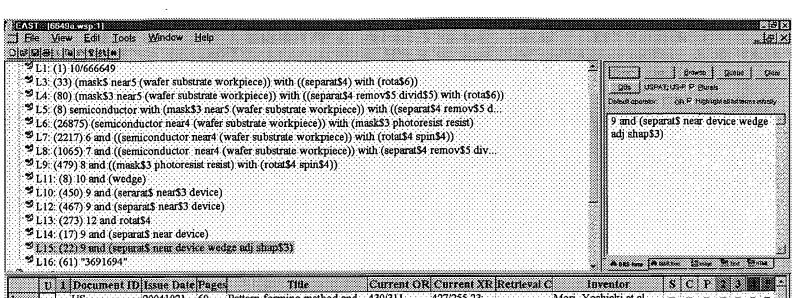


	1	Document II.	Issue Date	Pages	Title	Current OF	Current XR Retrieval C	<u> </u>	SCP23
, f	- r	US 6756611	20040629	37	Nitride semiconductor growth	257/103	257/13;	Kiyoku, Hiroyuki et al.	<b>#</b>
r	Г	US 6633081	20031014	14		257/738	257/777;	Sahara, Ryuiti et al.	
,	- г	US 6497784	20021224	10	Semiconductor wafer edge	156/345.12	257/E21.244	Jones, Bradley P. et al.	жссссс
r	г г	US 6251250	20010626	17	Method of and apparatus for	205/89	204/224R;	Keigler, Arthur	<b>8</b>
,	7 6	US 6176967	20010123	5	Reactive ion etch chamber	156/345.3	904/22A.0t	Obszarny, Christopher	*
i i	C	US 6153010 A	20001128	35	Method of growing nitride	117/95	117/106;	Kiyoku, Hiroyuki et al.	8 6 6 6 6 6
ı		US 6117778 A	20000912	10	Semiconductor wafer edge	438/692	257/E21.244;	Jones, Bradley P. et al.	គេ០០០០០
,	c c	US 5874329 A	19990223	11	Method for	438/203	257/E21.345;	Neary, Paul et al.	8 c c c c c
ı		US 5858112 A	19990112	16	Method for cleaning	134/6	134/32;	Yonemizu, Akira et al.	e c c c c c
1	- r	US 5830799 A	19981103	24	Method for forming	438/401	148/DIG 102;	Ammo, Hiroaki et al.	e r r r r r
1		US 5651160 A	19970729	16	Cleaning apparatus for	15/302	134/902;	Yonemizu, Akira et al.	proppod
ı		US 5491109 A	19960213	15	Method for the construction	438/624	257/E21.576;	Kim, Jae G:	er r r r r
ſ	r	US 4876216 A	19891024	7	Semiconductor integrated	438/437	257/E21.548;	Tobias, Eric et al.	errrrr
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	U	1	Document II)	Issue Date	Pages	Title	Current OR	Current XR Retrieval C	inventor	S C P 2 3 2 2
1	٢		US	20041021	60	\$` <del></del>		427/255.23;	Mori, Yoshiaki et al.	<b>8</b>
2	г	r	US	20040624	10	Angled wafer rotating ion	438/302		Wang, Tzu-Yu	errerr
9	٣	٣	00040101551 US	20040520	38	Nitride semiconductor growth	la a a alalah alalah biri	257/627;	Kiyoku, Hiroyuki et al.	* c c c c c c
1	г		US	20040325	8	\$ TO TOTAL	438/540	257ff21 100	Molina, Michael	
5	r	г	US	20040304	97		430/22	250/396R;	Takeishi, Tomoyuki et	* c c c c c c
,	r.	r	US	20030306			430/325	396/611;	Yoshihara, Kousuke et	<b>&amp;</b>
	r	г	US US	20030227	37	Nitride semiconductor growth		257/E21.108;	Kiyoku, Hiroyuki et al.	R C C E C C E
	г	г	US	20021205	16	Semiconductor device and	257/738	257/E23 178	Sahara, Ryuiti et al.	errcrr;
	r		20020180041 US	20020425	42	Nitride semiconductor growth		257/E21.108;	Kiyoku, Hiroyuki et al.	R C C C C C C
0	г	۲.	US 6756611	20040629	37	Nitride semiconductor growth			Kiyoku, Hiroyuki et al.	er cocc
1	r	г	US 6633081	20031014	14	Semiconductor device on a		257/777;	Sahara, Ryuiti et al.	P C C C C C C
2			US 6497784	20021224	10	\$5 \$17 i 7 i i i i i i i i i i i i i i i i i	156/345.12	257/E21.244	Jones, Bradley P. et al.	* r r r r r r
3	٢	r	US 6251250	20010626	17	Method of and apparatus for	155.51.13.1.1.1.1.1.1.1.	204/224R;	Keigler, Arthur	8 C C C C C C
4	٣	r	US 6176967	20010123	5	Reactive ion etch chamber	156/345.3	204/224-1	Obszarny, Christopher	errere. I